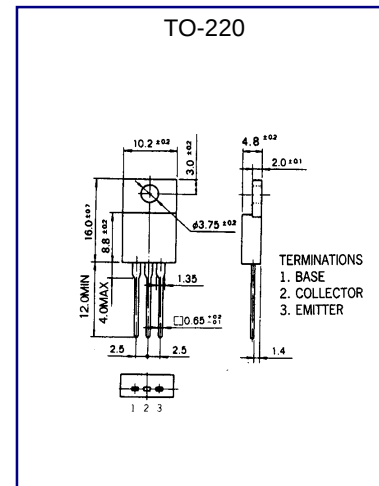




BU406D

NPN EPITAXIAL SILICON TRANSISTOR

HIGH VOLTAGE SWITCHING USE IN
HORIZONTAL DEFLECTION OUTPUT STAGE



ABSOLUTE MAXIMUM RATINGS ($T_a=25^{\circ}\text{C}$)

Characteristic	Symbol	Rating	Unit
Collector-Base Voltage	VCBO	400	V
Collector-Emitter Voltage	VCEO	400	V
Emitter-Base voltage	VEBO	6	V
Collector Current (DC)	IC	7	A
Collector Peak Current	ICM	10	A
Base Current (DC)	IB	4	A
Collector Dissipation ($T_c=25^{\circ}\text{C}$)	PC	60	W
Junction Temperature	Tj	150	$^{\circ}\text{C}$
Storage Temperature	Tstg	-65~150	$^{\circ}\text{C}$

ELECTRICAL CHARACTERISTICS ($T_a=25^{\circ}\text{C}$)

Characteristic	Symbol	Test Condition	Min	Typ	Max	Unit
Collector Cutoff Current ($V_{BE}=0$)	ICES	$V_{CE}=400\text{V}$, $V_{EB}=0$			5	mA
Emitter Cutoff Current ($I_C=0$)	IEBO	$V_{EB}=6\text{V}$, $I_C=0$			1	mA
Collector Emitter Saturation Voltage	$V_{CE(sat)}$	$I_C=5\text{A}$, $I_B=0.5\text{A}$			1.2	V
Base- Emitter Saturation Voltage	$V_{BE(sat)}$	$I_C=5\text{A}$, $I_B=1.2\text{A}$			1.5	V
Current Gain Bandwidth Product	fT	$V_{CE}=10\text{V}$, $I_C=500\text{mA}$	10			MHZ
Turn-Off Time	toff	$I_C=5\text{A}$, $I_B=0.5\text{A}$			0.75	μS
		$I_C=5\text{A}$, $I_B=0.8\text{A}$			0.4	μS
		$I_C=6\text{A}$, $I_B=1.2\text{A}$			0.4	μS